

Nominal Frequency 25.03875MHz

#### T TS -25.03875M EH25 45

Series -RoHS Compliant (Pb-free) 5.0V 4 Pad 5mm x 7mm Ceramic SMD HCMOS/TTL High Frequency Oscillator

Frequency Tolerance/Stability ±50ppm Maximum

Operating Te 0°C to +70°C

Pin 1 Connection Tri-State (High Impedance)

ating	Temperature	Range	•
o 170	°C		

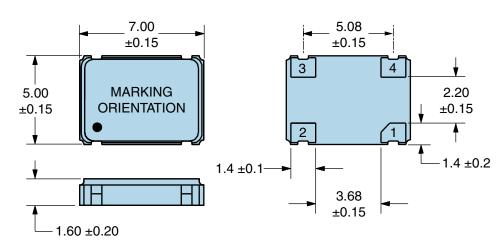
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L	Duty Cycle 50 ±5(%)		

Nominal Frequency	25.03875MHz
Frequency Tolerance/Stability	±50ppm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Output Load Change, First Year Aging at 25°C, Shock, and Vibration)
Aging at 25°C	±5ppm/year Maximum
Operating Temperature Range	0°C to +70°C
Supply Voltage	5.0Vdc ±10%
Input Current	50mA Maximum (No Load)
Output Voltage Logic High (Voh)	2.4Vdc Minimum with TTL Load, Vdd-0.4Vdc Minimum with HCMOS Load (IOH= -16mA)
Output Voltage Logic Low (Vol)	0.4Vdc Maximum with TTL Load, 0.5Vdc Maximum with HCMOS Load (IOH= +16mA)
Rise/Fall Time	6nSec Maximum (Measured at 0.8Vdc to 2.0Vdc with TTL Load; Measured at 20% to 80% of waveform with HCMOS Load)
Duty Cycle	50 ±5(%) (Measured at 50% of waveform with TTL Load or with HCMOS Load)
Load Drive Capability	10TTL Load or 50pF HCMOS Load Maximum
Output Logic Type	CMOS
Pin 1 Connection	Tri-State (High Impedance)
Tri-State Input Voltage (Vih and Vil)	+2.2Vdc Minimum to enable output, +0.8Vdc Maximum to disable output (High Impedance), No Connect to enable output.
Absolute Clock Jitter	±250pSec Maximum, ±100pSec Typical
One Sigma Clock Period Jitter	±50pSec Maximum, ±30pSec Typical
Start Up Time	10mSec Maximum
Storage Temperature Range	-55°C to +125°C

#### ENVIRONMENTAL & MECHANICAL SPECIFICATIONS

MIL-STD-883, Method 3015, Class 1, HBM: 1500V
MIL-STD-883, Method 1014, Condition A
UL94-V0
MIL-STD-883, Method 1014, Condition C
MIL-STD-883, Method 2002, Condition B
MIL-STD-883, Method 1004
J-STD-020, MSL 1
MIL-STD-202, Method 210, Condition K
MIL-STD-202, Method 215
MIL-STD-883, Method 2003
MIL-STD-883, Method 1010, Condition B
MIL-STD-883, Method 2007, Condition A

### **MECHANICAL DIMENSIONS (all dimensions in millimeters)**



PIN	CONNECTION
1	Tri-State
2	Ground
3	Output
4	Supply Voltage
LINE	MARKING
1	ECLIPTEK
2	25.038M
3	XXXXXX

#### Suggested Solder Pad Layout

All Dimensions in Millimeters

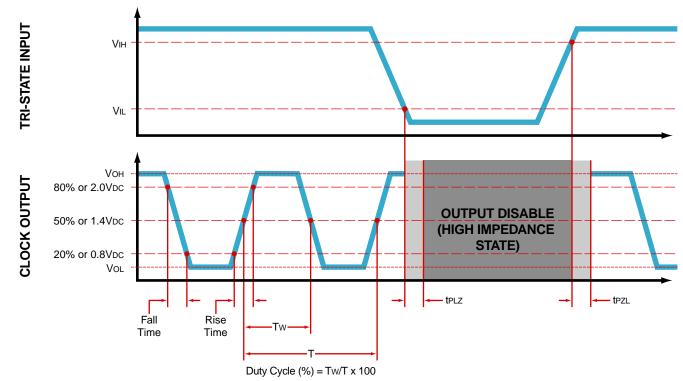


All Tolerances are ±0.1





#### **OUTPUT WAVEFORM & TIMING DIAGRAM**

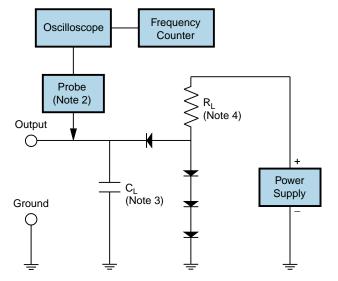


#### Test Circuit for TTL Output

Output Load Drive Capability	R <sub>L</sub> Value (Ohms)	C <sub>L</sub> Value (pF)
10TTL	390	15
5TTL	780	15
2TTL	1100	6
10LSTTL	2000	15
1TTL	2200	3







Note 1: An external 0.1µF low frequency tantalum bypass capacitor in parallel with a 0.01µF high frequency ceramic bypass capacitor close to the package ground and V<sub>DD</sub> pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth

(>300MHz) passive probe is recommended.

Note 3: Capacitance value  $C_L$  includes sum of all probe and fixture capacitance.

Note 4: Resistance value R<sub>L</sub> is shown in Table 1. See applicable specification sheet for 'Load Drive Capability'.

Note 5: All diodes are MMBD7000, MMBD914, or equivalent.



### **Test Circuit for CMOS Output**



Note 1: An external 0.1µF low frequency tantalum bypass capacitor in parallel with a 0.01µF high frequency ceramic bypass capacitor close to the package ground and V<sub>DD</sub> pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value  $\dot{C}_1$  includes sum of all probe and fixture capacitance.



# **Recommended Solder Reflow Methods**

EH2545TTS-25.03875M



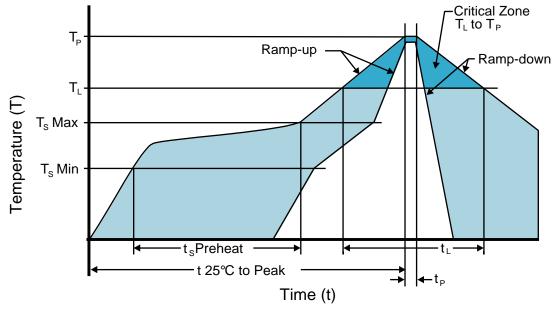
### **High Temperature Infrared/Convection**

$T_s$ MAX to $T_L$ (Ramp-up Rate)	3°C/second Maximum
Preheat	
- Temperature Minimum (T <sub>s</sub> MIN)	150°C
<ul> <li>Temperature Typical (T<sub>s</sub> TYP)</li> </ul>	175°C
<ul> <li>Temperature Maximum (T<sub>s</sub> MAX)</li> </ul>	200°C
- Time (t <sub>s</sub> MIN)	60 - 180 Seconds
Ramp-up Rate (T <sub>L</sub> to T <sub>P</sub> )	3°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	217°C
- Time (t∟)	60 - 150 Seconds
Peak Temperature (T <sub>P</sub> )	260°C Maximum for 10 Seconds Maximum
Target Peak Temperature (T <sub>P</sub> Target)	250°C +0/-5°C
Time within 5°C of actual peak (t <sub>p</sub> )	20 - 40 seconds
Ramp-down Rate	6°C/second Maximum
Time 25°C to Peak Temperature (t)	8 minutes Maximum
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.



# **Recommended Solder Reflow Methods**

EH2545TTS-25.03875M



### Low Temperature Infrared/Convection 240°C

$T_s$ MAX to $T_L$ (Ramp-up Rate)	5°C/second Maximum
Preheat	
- Temperature Minimum (T <sub>s</sub> MIN)	N/A
- Temperature Typical (T <sub>s</sub> TYP)	150°C
- Temperature Maximum (T <sub>s</sub> MAX)	N/A
- Time (t <sub>s</sub> MIN)	60 - 120 Seconds
Ramp-up Rate (T⊾ to T <sub>P</sub> )	5°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	150°C
- Time (t∟)	200 Seconds Maximum
Peak Temperature (T <sub>P</sub> )	240°C Maximum
Target Peak Temperature (T <sub>P</sub> Target)	240°C Maximum 1 Time / 230°C Maximum 2 Times
Time within 5°C of actual peak (t <sub>p</sub> )	10 seconds Maximum 2 Times / 80 seconds Maximum 1 Time
Ramp-down Rate	5°C/second Maximum
Time 25°C to Peak Temperature (t)	N/A
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.

#### Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

### High Temperature Manual Soldering

260°C Maximum for 5 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)